

300 mA, Low Voltage, Low Quiescent Current LDO Regulator

Features

- · 300 mA Output Current Capability
- Input Operating Voltage Range: 2.1V to 6.0V
- Adjustable Output Voltage Range: 0.8V to 5.0V (MCP1824 only)
- · Standard Fixed Output Voltages:
 - 0.8V, 1.2V, 1.8V, 2.5V, 3.0V, 3.3V, 5.0V
- Other Fixed Output Voltage Options Available Upon Request
- · Low Dropout Voltage: 200 mV Typical at 300 mA
- Typical Output Voltage Tolerance: 0.4%
- Stable with 1.0 µF Ceramic Output Capacitor
- · Fast Response to Load Transients
- Low Supply Current: 120 μA (typical)
- Low Shutdown Supply Current: 0.1 µA (typical) (MCP1824 only)
- Fixed Delay on Power Good Output (MCP1824 only)
- Short Circuit Current Limiting and Overtemperature Protection
- 5-Lead Plastic SOT-223, SOT-23 Package Options (MCP1824)
- 3-Lead Plastic SOT-223 Package Option (MCP1824S)

Applications

- · High-Speed Driver Chipset Power
- · Networking Backplane Cards
- · Notebook Computers
- · Network Interface Cards
- · Palmtop Computers
- · 2.5V to 1.XV Regulators

Description

The MCP1824/MCP1824S is a 300 mA Low Dropout (LDO) linear regulator that provides high current and low output voltages. The MCP1824 comes in a fixed or adjustable output voltage version, with an output voltage range of 0.8V to 5.0V. The 300 mA output current capability, combined with the low output voltage capability, make the MCP1824 a good choice for new sub-1.8V output voltage LDO applications that have high current demands. The MCP1824S is a 3-pin fixed voltage version.

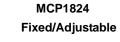
The MCP1824/MCP1824S is stable using ceramic output capacitors that inherently provide lower output noise and reduce the size and cost of the entire regulator solution. Only 1 µF of output capacitance is needed to stabilize the LDO.

Using CMOS construction, the quiescent current consumed by the MCP1824/MCP1824S is typically less than 120 μA over the entire input voltage range, making it attractive for portable computing applications that demand high output current. The MCP1824 versions have a Shutdown (\overline{SHDN}) pin. When shut down, the quiescent current is reduced to less than 0.1 μA .

On the MCP1824 fixed output versions, the scaled-down output voltage is internally monitored and a power good (PWRGD) output is provided when the output is within 92% of regulation (typical). The PWRGD delay is internally fixed at 110 µs (typical).

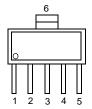
The overtemperature and short circuit current-limiting provide additional protection for the LDO during system fault conditions.

Package Types







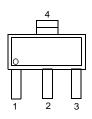




	SOT	-223	SOT-23		
Pin	Fixed Adjustable		Fixed	Adjustable	
1	SHDN	SHDN	V _{IN}	V _{IN}	
2	V_{IN}	V_{IN}	GND (TAB)	GND (TAB)	
3	GND (TAB)	GND (TAB)	SHDN	SHDN	
4	V _{OUT}	V _{OUT}	PWRGD	ADJ	
5	PWRGD	ADJ	V _{OUT}	V _{OUT}	
6	GND (TAB)	GND (TAB)			

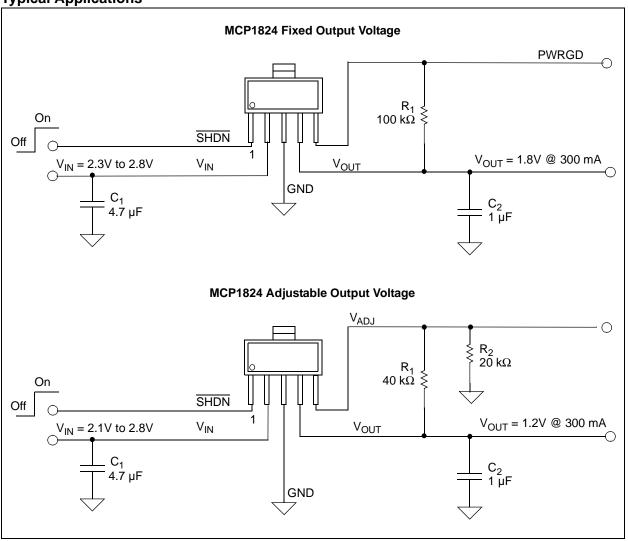
MCP1824S

SOT-223-3

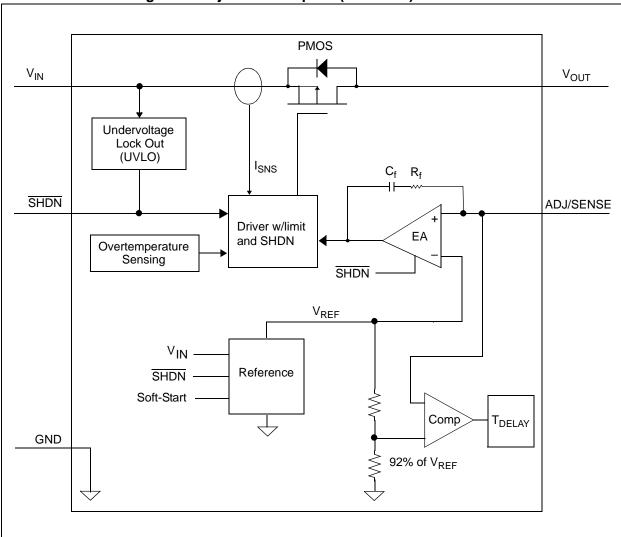


Pin	SOT-223
1	V _{IN}
2	GND (TAB)
3	V _{OUT}
4	GND (TAB)

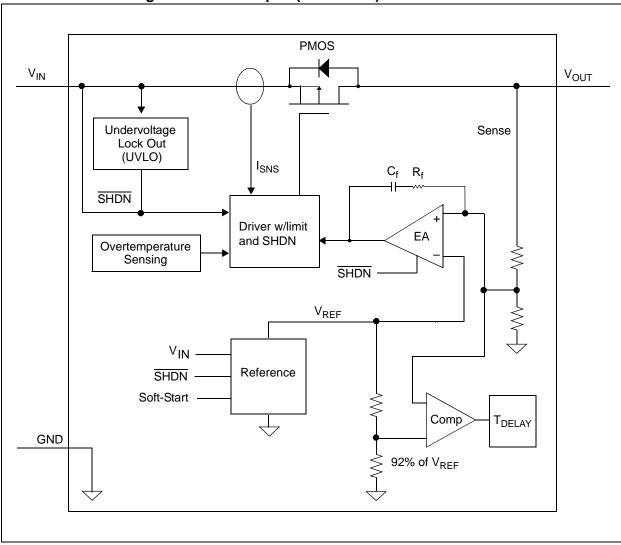
Typical Applications



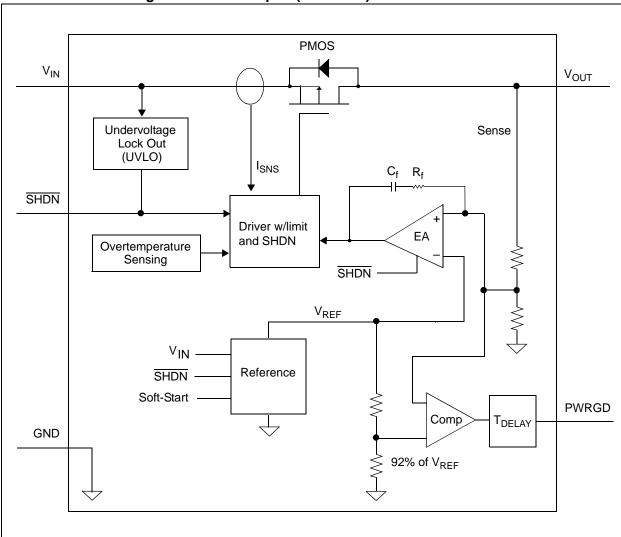
Functional Block Diagram - Adjustable Output (MCP1824)



Functional Block Diagram - Fixed Output (MCP1824S)



Functional Block Diagram - Fixed Output (MCP1824)



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

 $\label{eq:local_$

† Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

AC/DC CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, $V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}$, Note 1, $V_{R} = 1.8V$ for Adjustable Output, $I_{OUT} = 1$ mA, $C_{IN} = C_{OUT} = 4.7 \mu F$ (X7R Ceramic), $T_{A} = +25^{\circ}C$.

Boldface type applies for junction temperatures, T_{II} (Note 7) of -40°C to +125°C

Parameters	Sym	Min	Тур	Max	Units	Conditions
Input Operating Voltage	V _{IN}	2.1	_	6.0	V	
Output Voltage Range	V _{OUT}	0.8	_	5.0	V	
Input Quiescent Current	Iq	_	120	220	μA	$I_L = 0 \text{ mA}, V_{OUT} = 0.8V \text{ to}$ 5.0V
Input Quiescent Current for SHDN Mode	I _{SHDN}	_	0.1	3	μA	SHDN = GND
Maximum Continuous Output Current	I _{OUT}	300	_	_	mA	$V_{IN} = 2.1V \text{ to } 6.0V$ $V_{R} = 0.8V \text{ to } 5.0V$
Line Regulation	$\Delta V_{OUT}/$ $(V_{OUT} \times \Delta V_{IN})$	_	±0.05	±0. 17	%/V	(Note 1) $\leq V_{1N} \leq 6V$
Load Regulation	ΔV _{OUT} /V _{OUT}	-1.0	±0.5	1.0	%	I _{OUT} = 1 mA to 300 mA, (Note 4)
Output Short Circuit Current	I _{OUT_SC}	_	720	_	mA	$R_{LOAD} < 0.1\Omega$, Peak Current
Dropout Voltage	V _{DROPOUT}	_	200	320	mV	Note 5 , I _{OUT} = 300 mA, V _{IN(MIN)} = 2.1V
Pulsed Applications						
Maximum Pulsed Output Current	I _{PULSE}	_	500	_	mA	$\begin{split} &V_{\text{IN}} = 2.1 \text{V to } 6.0 \text{V} \\ &V_{\text{R}} = 0.8 \text{V to } 5.0 \text{V}, \\ &\text{Duty Cycle} \leq 60\%, \\ &\text{Period} < 10 \text{ ms} \end{split}$

- Note 1: The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.1 V$ and $V_{IN} \ge V_{OUT(MAX)} + V_{DROPOUT(MAX)}$.
 - 2: V_R is the nominal regulator output voltage for the fixed cases. $V_R = 1.2V$, 1.8V, etc. V_R is the desired set point output voltage for the adjustable cases. $V_R = V_{ADJ} \cdot ((R_1/R_2) + 1)$. Figure 4-1.
 - 3: $TCV_{OUT} = (V_{OUT-HIGH} V_{OUT-LOW}) *10^6 / (V_R * \Delta Temperature)$. $V_{OUT-HIGH}$ is the highest voltage measured over the temperature range. $V_{OUT-LOW}$ is the lowest voltage measured over the temperature range.
 - 4: Load regulation is measured at a constant junction temperature using low duty-cycle pulse testing. Load regulation is tested over a load range from 1 mA to the maximum specified output current.
 - 5: Dropout voltage is defined as the input-to-output voltage differential at which the output voltage drops 2% below its nominal value that was measured with an input voltage of V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}.
 - 6: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air. (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +150°C rating. Sustained junction temperatures above 150°C can impact device reliability.
 - 7: The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired junction temperature. The test time is small enough such that the rise in the junction temperature over the ambient temperature is not significant.

AC/DC CHARACTERISTICS (CONTINUED)

 $\textbf{Electrical Specifications:} \ \ \textbf{Unless otherwise noted}, \ \ \textbf{V}_{IN} = \textbf{V}_{OUT(MAX)} + \textbf{V}_{DROPOUT(MAX)}, \ \textbf{Note 1}, \ \textbf{V}_{R} = \textbf{1.8V} \ \ \text{for Adjustable Output}, \\ \textbf{V}_{IN} = \textbf{V}_{OUT(MAX)} + \textbf{V}_{DROPOUT(MAX)}, \ \ \textbf{V}_{R} = \textbf{1.8V} \ \ \textbf{V}_{R} = \textbf{$ $I_{OUT} = 1$ mA, $C_{IN} = C_{OUT} = 4.7 \mu F$ (X7R Ceramic), $T_A = +25$ °C.

Boldface type applies for junction temperatures, T_J (Note 7) of -40°C to +125°C

Parameters	Sym	Min	Тур	Max	Units	Conditions			
Maximum Pulsed Output Duty Cycle	I _{PULSE_DUTY}	_	_	60	%	V _{IN} = 2.1V to 6.0V, V _R = 0.8V to 5.0V, I _{OUT} = 500 mA, Period < 10 ms			
Maximum Pulsed Output Period	I _{PULSE_PERIOD}	_	_	10	ms	$V_{IN} = 2.1V \text{ to } 6.0V$ $V_{R} = 0.8V \text{ to } 5.0V,$ $I_{OUT} = 500 \text{ mA}$			
Adjust Pin Characteristics (Adjustable Output Only)									
Adjustable Output Voltage Range	V _{OUT_ADJ}	0.8	_	5.5	V				
Adjust Pin Reference Voltage	V_{ADJ}	0.402	0.410	0.418	V	V_{IN} = 2.1V to V_{IN} = 6.0V, I_{OUT} = 1 mA			
Adjust Pin Leakage Current	I _{ADJ}	-10	±0.01	+10	nA	$V_{IN} = 6.0V$, $V_{ADJ} = 0V$ to 6V			
Adjust Temperature Coefficient	TCV _{OUT}	_	40	_	ppm/°C	Note 3			
Fixed-Output Characteristics (F	ixed Output Only	·)							
Voltage Regulation	V _{OUT}	V _R - 2.5%	V _R ±0.5%	V _R + 2.5%	٧	Note 2			
Power Good Characteristics									
PWRGD Input Voltage Operat-	V _{PWRGD_VIN}	1.0	_	6.0	V	T _A = +25°C			
ing Range		1.2	_	6.0		$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			
						For V_{IN} < 2.1V, I_{SINK} = 100 μ A			
PWRGD Threshold Voltage	V _{PWRGD_TH}				%V _{OUT}	Falling Edge			
(Referenced to V _{OUT})		89	92	95		V _{OUT} < 2.5V Fixed, V _{OUT} = Adj.			
		90	92	94		V _{OUT} >= 2.5V Fixed			
PWRGD Threshold Hysteresis	V _{PWRGD_HYS}	1.0	2.0	3.0	%V _{OUT}				
PWRGD Output Voltage Low	V_{PWRGD_L}	_	0.05	0.4	V	I _{PWRGD SINK} = 1.2 mA, ADJ = 0V			
PWRGD Output Current Sink Capability	I _{PWRGD}	1.2	6.0	_	mA	V _{PWRGD} = 0.200V			
PWRGD Leakage	P _{WRGD-LK}	_	1	_	nA	$V_{PWRGD} = V_{IN} = 6.0V$			
PWRGD Time Delay	T _{PG}	_	110	_	μs	Rising Edge $R_{PULLUP} = 10 \text{ k}\Omega$			

- Note The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.1 \text{V}$ and $V_{IN} \ge V_{OUT(MAX)} + V_{DROPOUT(MAX)}$.
 - V_R is the nominal regulator output voltage for the fixed cases. $V_R = 1.2V$, 1.8V, etc. V_R is the desired set point output voltage for the adjustable cases. $V_R = V_{ADJ} * ((R_1/R_2) + 1)$. Figure 4-1. $TCV_{OUT} = (V_{OUT-HIGH} V_{OUT-LOW}) *10^6 / (V_R * \Delta Temperature)$. $V_{OUT-HIGH}$ is the highest voltage measured over the
 - temperature range. V_{OUT-LOW} is the lowest voltage measured over the temperature range.
 - Load regulation is measured at a constant junction temperature using low duty-cycle pulse testing. Load regulation is tested over a load range from 1 mA to the maximum specified output current.
 - Dropout voltage is defined as the input-to-output voltage differential at which the output voltage drops 2% below its nominal value that was measured with an input voltage of V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}.
 - The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air. (i.e., T_A , T_J , θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +150°C rating. Sustained junction temperatures above 150°C can impact device reliability.
 - The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired junction temperature. The test time is small enough such that the rise in the junction temperature over the ambient temperature is not significant.

AC/DC CHARACTERISTICS (CONTINUED)

Electrical Specifications: Unless otherwise noted, $V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}$, **Note 1**, $V_R = 1.8V$ for Adjustable Output, $I_{OUT} = 1$ mA, $C_{IN} = C_{OUT} = 4.7$ µF (X7R Ceramic), $T_A = +25$ °C.

Boldface type applies for junction temperatures, T_J (Note 7) of -40°C to +125°C

Parameters	Sym	Min	Тур	Max	Units	Conditions		
Detect Threshold to PWRGD Active Time Delay	T _{VDET-PWRGD}	_	200	_	μs	$V_{OUT} = V_{PWRGD_TH} + 50 \text{ mV}$ to $V_{PWRGD_TH} - 50 \text{ mV}$		
Shutdown Input								
Logic High Input	V _{SHDN-HIGH}	45	_	1	%V _{IN}	V _{IN} = 2.1V to 6.0V		
Logic Low Input	V _{SHDN-LOW}	_	_	15	%V _{IN}	V _{IN} = 2.1V to 6.0V		
SHDN Input Leakage Current	SHDN _{ILK}	-0.1	±0.001	+0.1	μA	$\frac{V_{IN} = 6V, \overline{SHDN} = V_{IN},}{\overline{SHDN} = GND}$		
AC Performance		l .						
Output Delay From SHDN	T _{OR}	_	100	_	μs	$\overline{SHDN} = GND \text{ to } V_{IN},$ $V_{OUT} = GND \text{ to } 95\% \text{ V}_{R}$		
Output Noise	e _N	_	2.0	-	μV/√Hz	$\begin{split} I_{OUT} &= 200 \text{ mA, f} = 1 \text{ kHz,} \\ C_{OUT} &= 10 \mu\text{F (X7R Ceramic),} \\ V_{OUT} &= 2.5 \text{V} \end{split}$		
Power Supply Ripple Rejection Ratio	PSRR	_	55	1	dB	$\begin{split} f &= 100 \text{ Hz}, \\ I_{OUT} &= 10 \text{ mA}, \\ V_{INAC} &= 200 \text{ mV pk-pk}, \\ C_{IN} &= 0 \mu\text{F} \end{split}$		
Thermal Shutdown Temperature	T _{SD}	_	150		°C	$I_{OUT} = 100 \mu A, V_{OUT} = 1.8V,$ $V_{IN} = 2.8V$		
Thermal Shutdown Hysteresis	ΔT_{SD}	_	10	_	°C	$I_{OUT} = 100 \mu A, V_{OUT} = 1.8V,$ $V_{IN} = 2.8V$		

Note 1: The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.1 V$ and $V_{IN} \ge V_{OUT(MAX)} + V_{DROPOUT(MAX)}$.

- 2: V_R is the nominal regulator output voltage for the fixed cases. $V_R = 1.2V$, 1.8V, etc. V_R is the desired set point output voltage for the adjustable cases. $V_R = V_{ADJ} \cdot ((R_1/R_2) + 1)$. Figure 4-1.
- 3: $TCV_{OUT} = (V_{OUT-HIGH} V_{OUT-LOW}) *10^6 / (V_R * \Delta Temperature)$. $V_{OUT-HIGH}$ is the highest voltage measured over the temperature range. $V_{OUT-LOW}$ is the lowest voltage measured over the temperature range.
- 4: Load regulation is measured at a constant junction temperature using low duty-cycle pulse testing. Load regulation is tested over a load range from 1 mA to the maximum specified output current.
- 5: Dropout voltage is defined as the input-to-output voltage differential at which the output voltage drops 2% below its nominal value that was measured with an input voltage of V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}.
- 6: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air. (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +150°C rating. Sustained junction temperatures above 150°C can impact device reliability.
- 7: The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired junction temperature. The test time is small enough such that the rise in the junction temperature over the ambient temperature is not significant.

TEMPERATURE SPECIFICATIONS

Parameters	Sym	Min	Тур	Max	Units	Conditions	
Temperature Ranges							
Operating Junction Temperature Range	T_J	-40	_	+125	°C	Steady State	
Maximum Junction Temperature	T_J	_	_	+150	°C	Transient	
Storage Temperature Range	T _A	-65	_	+150	°C		
Thermal Package Resistances							
Thermal Resistance, 3LD SOT-223	θ_{JA}	_	62	_	°C/W	EIA/JEDEC JESD51-751-7	
	θ_{JC}	_	15	_		4 Layer Board	
Thermal Resistance, 5LD SOT-23	θ_{JA}	_	256	_	°C/W	EIA/JEDEC JESD51-751-7	
	θ_{JC}	_	81	_		4 Layer Board	
Thermal Resistance, 5LD SOT-223	θ_{JA}	_	62	_	°C/W	EIA/JEDEC JESD51-751-7	
	θ_{JC}	_	15	_		4 Layer Board	

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, C_{OUT} = 4.7 μF Ceramic (X7R), C_{IN} = 4.7 μF Ceramic (X7R), I_{OUT} = 1 mA, Temperature = +25°C, V_{IN} = V_{OUT} + 0.5V, Fixed output, \overline{SHDN} = 10 $k\Omega$ pullup to V_{IN} .

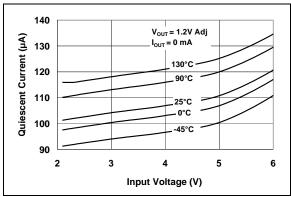


FIGURE 2-1: Quiescent Current vs. Input Voltage (Adjustable Version).

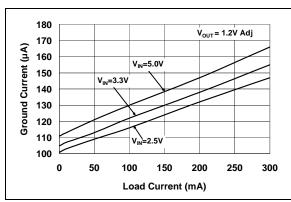


FIGURE 2-2: Ground Current vs. Load Current (Adjustable Version).

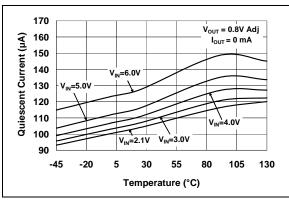


FIGURE 2-3: Quiescent Current vs. Junction Temperature (Adjustable Version).

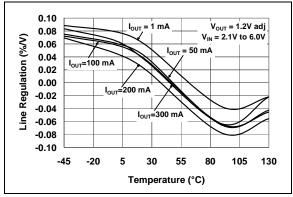


FIGURE 2-4: Line Regulation vs. Temperature (Adjustable Version).

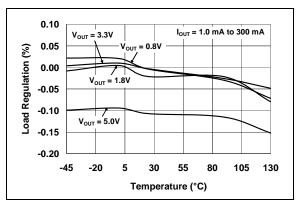


FIGURE 2-5: Load Regulation vs. Temperature (Adjustable Version).

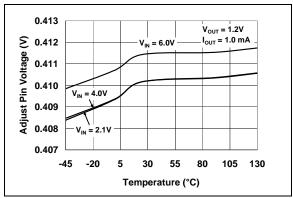


FIGURE 2-6: Adjust Pin Voltage vs. Temperature (Adjustable Version).

Note: Unless otherwise indicated, C_{OUT} = 4.7 μF Ceramic (X7R), C_{IN} = 4.7 μF Ceramic (X7R), I_{OUT} = 1 mA, Temperature = +25°C, V_{IN} = V_{OUT} + 0.5V, Fixed output, \overline{SHDN} = 10 kΩ pullup to V_{IN} .

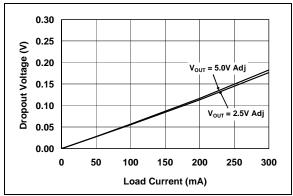


FIGURE 2-7: Dropout Voltage vs. Load Current (Adjustable Version).

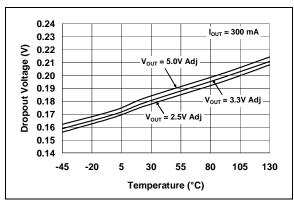


FIGURE 2-8: Dropout Voltage vs. Temperature (Adjustable Version).

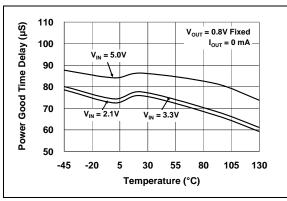


FIGURE 2-9: Power Good (PWRGD) Time Delay vs. Temperature.

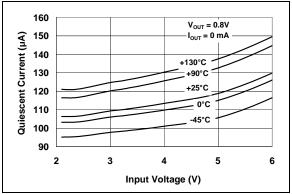


FIGURE 2-10: Quiescent Current vs. Input Voltage.

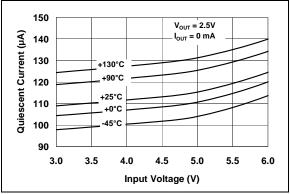


FIGURE 2-11: Quiescent Current vs. Input Voltage.

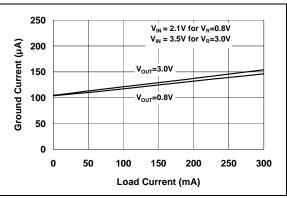


FIGURE 2-12: Ground Current vs. Load Current.

Note: Unless otherwise indicated, C_{OUT} = 4.7 μ F Ceramic (X7R), C_{IN} = 4.7 μ F Ceramic (X7R), I_{OUT} = 1 mA, Temperature = +25°C, V_{IN} = V_{OUT} + 0.5V, Fixed output, \overline{SHDN} = 10 $k\Omega$ pullup to V_{IN} .

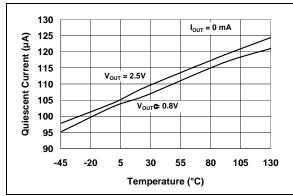


FIGURE 2-13: Quiescent Current vs. Temperature.

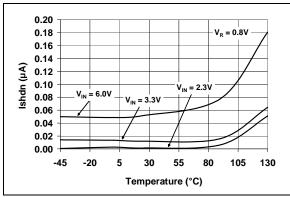


FIGURE 2-14: I_{SHDN} vs. Temperature.

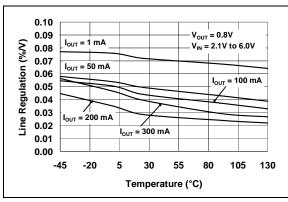


FIGURE 2-15: Line Regulation vs. Temperature.

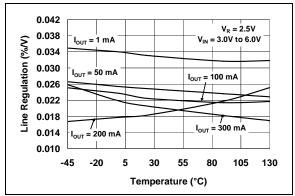


FIGURE 2-16: Line Regulation vs. Temperature.

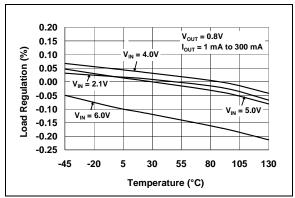


FIGURE 2-17: Load Regulation vs. Temperature.

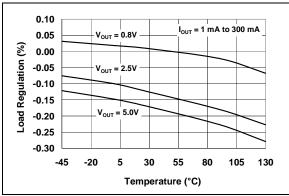


FIGURE 2-18: Load Regulation vs. Temperature.

Note: Unless otherwise indicated, $C_{OUT} = 4.7 \ \mu F$ Ceramic (X7R), $C_{IN} = 4.7 \ \mu F$ Ceramic (X7R), $I_{OUT} = 1 \ mA$, Temperature = $+25^{\circ}C$, $V_{IN} = V_{OUT} + 0.5V$, Fixed output, $\overline{SHDN} = 10 \ k\Omega$ pullup to V_{IN} .

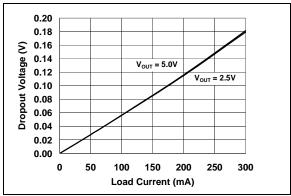


FIGURE 2-19: Dropout Voltage vs. Load Current.

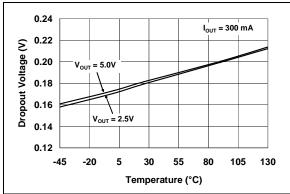


FIGURE 2-20: Dropout Voltage vs. Temperature.

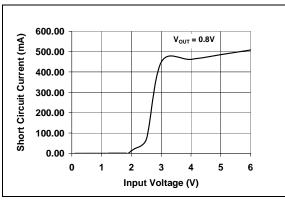


FIGURE 2-21: Short Circuit Current vs. Input Voltage.

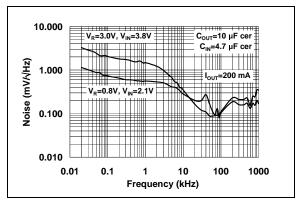


FIGURE 2-22: Output Noise Voltage Density vs. Frequency.

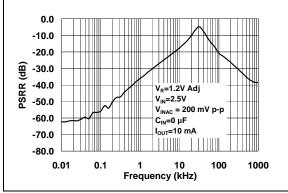


FIGURE 2-23: Power Supply Ripple Rejection (PSRR) vs. Frequency (Adj.).

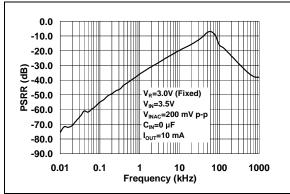


FIGURE 2-24: Power Supply Ripple Rejection (PSRR) vs. Frequency.

Note: Unless otherwise indicated, C_{OUT} = 4.7 μF Ceramic (X7R), C_{IN} = 4.7 μF Ceramic (X7R), I_{OUT} = 1 mA, Temperature = +25°C, V_{IN} = V_{OUT} + 0.5V, Fixed output, \overline{SHDN} = 10 kΩ pullup to V_{IN} .

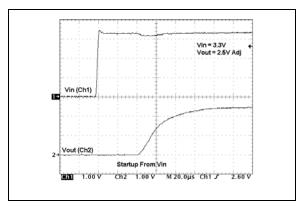


FIGURE 2-25: Startup from V_{IN} (Adjustable Version).

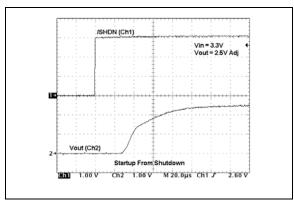


FIGURE 2-26: Startup from Shutdown (Adjustable Version).

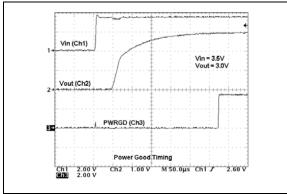


FIGURE 2-27: Power Good (PWRGD) Timing.

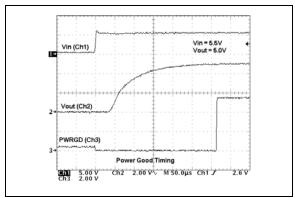


FIGURE 2-28: Power Good (PWRGD) Timing.

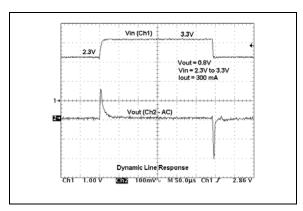


FIGURE 2-29: Dynamic Line Response.

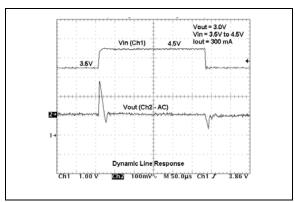


FIGURE 2-30: Dynamic Line Response.

Note: Unless otherwise indicated, C_{OUT} = 4.7 μF Ceramic (X7R), C_{IN} = 4.7 μF Ceramic (X7R), I_{OUT} = 1 mA, Temperature = +25°C, V_{IN} = V_{OUT} + 0.5V, Fixed output, \overline{SHDN} = 10 kΩ pullup to V_{IN} .

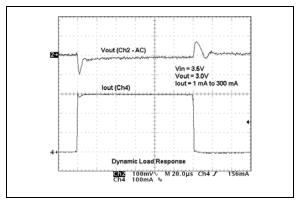


FIGURE 2-31: Dynamic Load Response.

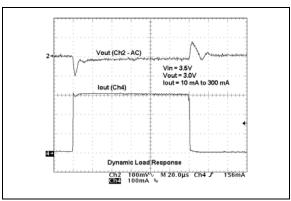


FIGURE 2-32: Dynamic Load Response.

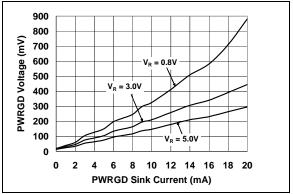


FIGURE 2-33: Power Good Pulldown Voltage Vs Load.

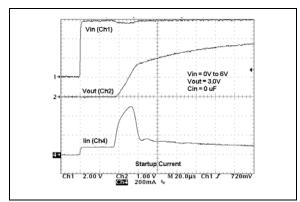


FIGURE 2-34: Startup Current.

3.0 PIN DESCRIPTION

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

	SOT-223		so	Г-23		
3-Pin Fixed	5-Pin Fixed	5-Pin Adj	5-Pin Fixed	5-Pin Adj	Name	Description
_	1	1	3	3	SHDN	Shutdown Control Input (active-low)
1	2	2	1	1	V _{IN}	Input Voltage Supply
2	3	3	2	2	GND	Ground
3	4	4	5	5	V _{OUT}	Regulated Output Voltage
_	5	_	4	_	PWRGD	Power Good Output
_	ı	5		4	ADJ	Output Voltage Adjust/Sense Input
Exposed Pad	Exposed Pad	Exposed Pad			EP	Exposed Pad of the Package (ground potential)

3.1 Shutdown Control Input (SHDN)

The \overline{SHDN} input is used to turn the LDO output voltage on and off. When the \overline{SHDN} input is at a logic-high level, the LDO output voltage is enabled. When the \overline{SHDN} input is pulled to a logic-low level, the LDO output voltage is disabled. When the \overline{SHDN} input is pulled low, the PWRGD output also goes low and the LDO enters a low quiescent current shutdown state where the typical quiescent current is 0.1 μ A.

3.2 Input Voltage Supply (V_{IN})

Connect the unregulated or regulated input voltage source to $V_{IN}.$ If the input voltage source is located several inches away from the LDO, or the input source is a battery, it is recommended that an input capacitor be used. A typical input capacitance value of 1 μF to 10 μF should be sufficient for most applications. The type of capacitor used can be ceramic, tantalum, or aluminum electrolytic. The low ESR characteristics of the ceramic capacitor will yield better noise and PSRR performance at high frequency.

3.3 Ground (GND)

For the optimal Noise and Power Supply Rejection Ratio (PSRR) performance, the GND pin of the LDO should be tied to an electrically quiet circuit ground. This will help the LDO power supply rejection ratio and noise performance. The ground pin of the LDO only conducts the ground current of the LDO, so a heavy trace is not required. For applications that have switching or noisy inputs, tie the GND pin to the return of the output capacitor. Ground planes help lower inductance and voltage spikes caused by fast transient load currents and are recommended for applications that are subjected to fast load transients.

3.4 Regulated Output Voltage (V_{OUT})

The V_{OUT} pin is the regulated output voltage of the LDO. A minimum output capacitance of 1.0 μ F is required for LDO stability. The MCP1824/MCP1824S is stable with ceramic, tantalum, and aluminum-electrolytic capacitors. See **Section 4.3** "**Output Capacitor**" for output capacitor selection guidance.

3.5 Power Good Output (PWRGD)

For fixed applications, the PWRGD output is an opendrain output used to indicate when the LDO output voltage is within 92% (typically) of its nominal regulation value. The PWRGD threshold has a typical hysteresis value of 2%. The PWRGD output is delayed by 110 μs (typical) from the time the LDO output is within 92% + 3% (maximum hysteresis) of the regulated output value on power-up. This delay time is internally fixed.

3.6 Output Voltage Adjust Input (ADJ)

For adjustable applications, the output voltage is connected to the ADJ input through a resistor divider that sets the output voltage regulation value. This provides the users the capability to set the output voltage to any value they desire within the 0.8V to 5.0V range of the device.

3.7 Exposed Pad (EP)

The SOT-223 package has an exposed metal pad on the bottom of the package. The exposed metal pad gives the device better thermal characteristics by providing a good thermal path to either the PCB or heatsink to remove heat from the device. The exposed pad of the package is at ground potential.

4.0 DEVICE OVERVIEW

The MCP1824/MCP1824S is a 300 mA output current, Low Dropout (LDO) voltage regulator. The low dropout voltage of 200 mV typical at 300 mA of current makes it ideal for battery-powered applications. The input voltage range is 2.1V to 6.0V. Unlike other high output current LDOs, the MCP1824/MCP1824S only draws a maximum of 220 μA of quiescent current. The MCP1824 adds a shutdown control input pin and a power good output pin. The two output voltage options are fixed or adjustable. The adjustable output voltage is set using two external resistors.

4.1 LDO Output Voltage

The MCP1824 LDO is available with either a fixed output voltage or an adjustable output voltage. The output voltage range is 0.8V to 5.0V for either version. The MCP1824S LDO is available as a fixed voltage device.

4.1.1 ADJUST INPUT

The adjustable version of the MCP1824 uses the ADJ pin to get the output voltage feedback for output voltage regulation. This allows the user to set the output voltage of the device with two external resistors. The nominal voltage for ADJ is 0.41V.

Figure 4-1 shows the adjustable version of the MCP1824. Resistors R_1 and R_2 form the resistor divider network necessary to set the output voltage. With this configuration, Equation 4-1 represents the equation for setting V_{OLIT} .

EQUATION 4-1: CALCULATING VOLIT

$$V_{OUT} = V_{ADJ} \left(\frac{R_1 + R_2}{R_2} \right)$$

Where:

V_{OUT} = LDO Output Voltage V_{ADJ} = ADJ Pin Voltage (typically 0.41V)

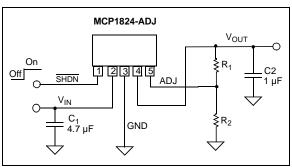


FIGURE 4-1: Typical Adjustable Output Voltage Application Circuit.

The allowable resistance value range for resistor R_2 is from 10 k Ω to 200 k Ω . Solving Equation 4-1 for R_1 yields Equation 4-2.

EQUATION 4-2: CALCULATING ADJ PIN RESISTOR VALUES

$$R_1 = R_2 \left(\frac{V_{OUT}}{V_{ADJ}} - I \right)$$

Where:

V_{OUT} = LDO Output Voltage V_{ADJ} = ADJ Pin Voltage (typically 0.41V)

4.2 Output Current and Current Limiting

The MCP1824/MCP1824S LDO is tested and ensured to supply a minimum of 300 mA of output current. The MCP1824/MCP1824S has no minimum output load, so the output load current can go to 0 mA and the LDO will continue to regulate the output voltage to within tolerance.

The MCP1824/MCP1824S also incorporates an output current limit. If the output voltage falls below 0.7V due to an overload condition (usually represents a shorted load condition), the output current is limited to 720 mA (typical). If the overload condition is a soft overload, the MCP1824/MCP1824S will supply higher load currents of up to 900 mA. The MCP1824/MCP1824S should not be operated in this condition continuously as it may result in failure of the device. However, this does allow for device usage in applications that have higher pulsed load currents having an average output current value of 300 mA or less.

Output overload conditions may also result in an overtemperature shutdown of the device. If the junction temperature rises above 150°C (typical), the LDO will shut down the output voltage. See **Section 4.8 "Overtemperature Protection"** for more information on overtemperature shutdown.

4.3 Output Capacitor

The MCP1824/MCP1824S requires a minimum output capacitance of 1 μ F for output voltage stability. Ceramic capacitors are recommended because of their size, cost, and environmental robustness qualities.

Aluminum-electrolytic and tantalum capacitors can be used on the LDO output as well. The Equivalent Series Resistance (ESR) of the electrolytic output capacitor must be no greater than 1 ohm. The output capacitor should be located as close to the LDO output as is practical. Ceramic materials X7R and X5R have low temperature coefficients and are well within the acceptable ESR range required. A typical 1 μF X7R 0805 capacitor has an ESR of 50 milli-ohms.

Larger LDO output capacitors can be used with the MCP1824/MCP1824S to improve dynamic performance and power supply ripple rejection performance. A maximum of 22 μ F is recommended. Aluminum-electrolytic capacitors are not recommended for low temperature applications of < -25°C.

4.4 Input Capacitor

Low input source impedance is necessary for the LDO output to operate properly. When operating from batteries, or in applications with long lead length (> 10 inches) between the input source and the LDO, some input capacitance is recommended. A minimum of 1.0 μF to 4.7 μF is recommended for most applications.

For applications that have output step load requirements, the input capacitance of the LDO is very important. The input capacitance provides the LDO with a good local low-impedance source to pull the transient currents from, in order to respond quickly to the output load step. For good step response performance, the input capacitor should be of equivalent (or higher) value than the output capacitor. The capacitor should be placed as close to the input of the LDO as is practical. Larger input capacitors will also help reduce any high-frequency noise on the input and output of the LDO and reduce the effects of any inductance that exists between the input source voltage and the input capacitance of the LDO.

4.5 Power Good Output (PWRGD)

The PWRGD output is used to indicate when the output voltage of the LDO is within 92% (typical value, see **Section 1.0 "Electrical Characteristics"** for Minimum and Maximum specifications) of its nominal regulation value.

As the output voltage of the LDO rises, the PWRGD output will be held low until the output voltage has exceeded the power good threshold plus the hysteresis value. Once this threshold has been exceeded, the power good time delay is started (shown as T_{PG} in the Electrical Characteristics table). The power good time

delay is fixed at $110 \,\mu s$ (typical). After the time delay period, the PWRGD output will go high, indicating that the output voltage is stable and within regulation limits.

If the output voltage of the LDO falls below the power good threshold, the power good output will transition low. The power good circuitry has a 200 µs delay when detecting a falling output voltage, which helps to increase noise immunity of the power good output and avoid false triggering of the power good output during fast output transients. See Figure 4-2 for power good timing characteristics.

When the LDO is put into Shutdown mode using the SHDN input, the power good output is pulled low immediately, indicating that the output voltage will be out of regulation. The timing diagram for the power good output when using the shutdown input is shown in Figure 4-3.

The power good output is an open-drain output that can be pulled up to any voltage that is equal to or less than the LDO input voltage. This output is capable of sinking 1.2 mA minimum ($V_{PWRGD} < 0.4V$ maximum).

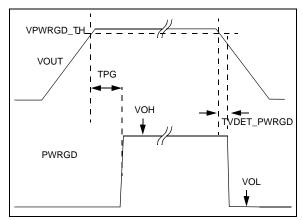


FIGURE 4-2: Power Good Timing.

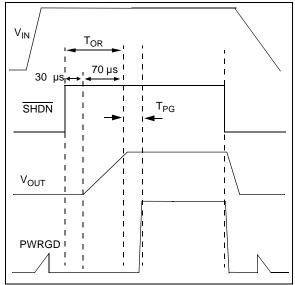


FIGURE 4-3: Power Good Timing from Shutdown.

4.6 Shutdown Input (SHDN)

The \overline{SHDN} input is an active-low input signal that turns the LDO on and off. The \overline{SHDN} threshold is a percentage of the input voltage. The typical value of this shutdown threshold is 30% of V_{IN} , with minimum and maximum limits over the entire operating temperature range of 45% and 15%, respectively.

The SHDN input will ignore low-going pulses (pulses meant to shut down the LDO) that are up to 400 ns in pulse width. If the shutdown input is pulled low for more than 400 ns, the LDO will enter Shutdown mode. This small bit of filtering helps to reject any system noise spikes on the shutdown input signal.

On the rising edge of the \overline{SHDN} input, the shutdown circuitry has a 30 µs delay before allowing the LDO output to turn on. This delay helps to reject any false turn-on signals or noise on the \overline{SHDN} input signal. After the 30 µs delay, the LDO output enters its soft-start period as it rises from 0V to its final regulation value. If the \overline{SHDN} input signal is pulled low during the 30 µs delay period, the timer will be reset and the delay time will start over again on the next rising edge of the \overline{SHDN} input. The total time from the \overline{SHDN} input going high (turn-on) to the LDO output being in regulation is typically 100 µs. See Figure 4-4 for a timing diagram of the \overline{SHDN} input.

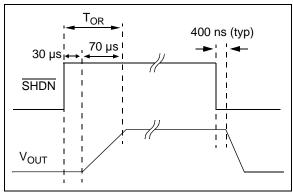


FIGURE 4-4: Shutdown Input Timing Diagram.

4.7 Dropout Voltage and Undervoltage Lockout

Dropout voltage is defined as the input-to-output voltage differential at which the output voltage drops 2% below the nominal value that was measured with a $V_R + 0.5V$ differential applied. The MCP1824/ MCP1824S LDO has a very low dropout voltage specification of 210 mV (typical) at 300 mA of output current. See **Section 1.0** "Electrical Characteristics" for maximum dropout voltage specifications.

The MCP1824/MCP1824S LDO operates across an input voltage range of 2.1V to 6.0V and incorporates input Undervoltage Lockout (UVLO) circuitry that keeps the LDO output voltage off until the input voltage reaches a minimum of 2.00V (typical) on the rising edge of the input voltage. As the input voltage falls, the LDO output will remain on until the input voltage level reaches 1.82V (typical).

Since the MCP1824/MCP1824S LDO undervoltage lockout activates at 1.82V as the input voltage is falling, the dropout voltage specification does not apply for output voltages that are less than 1.8V.

For high-current applications, voltage drops across the PCB traces must be taken into account. The trace resistances can cause significant voltage drops between the input voltage source and the LDO. For applications with input voltages near 2.1V, these PCB trace voltage drops can sometimes lower the input voltage enough to trigger a shutdown due to undervoltage lockout.

4.8 Overtemperature Protection

The MCP1824/MCP1824S LDO has temperature sensing circuitry to prevent the junction temperature from exceeding approximately 150°C. If the LDO junction temperature does reach 150°C, the LDO output will be turned off until the junction temperature cools to approximately 140°C, at which point the LDO output will automatically resume normal operation. If the internal power dissipation continues to be excessive, the device will again shut off. The junction temperature of the die is a function of power dissipation, ambient temperature and package thermal resistance. See **Section 5.0 "Application Circuits/Issues"** for more information on LDO power dissipation and junction temperature.

5.0 APPLICATION CIRCUITS/ ISSUES

5.1 Typical Application

The MCP1824/MCP1824S is used for applications that require high LDO output current and a power good output.

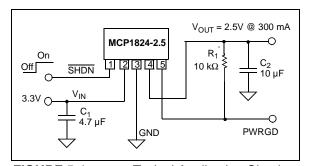


FIGURE 5-1: Typical Application Circuit.

5.1.1 APPLICATION CONDITIONS

Package Type = SOT-223-5 Input Voltage Range = $3.3V \pm 5\%$ V_{IN} maximum = 3.465V

 V_{IN} minimum = 3.135V $V_{DROPOUT (max)}$ = 0.350V V_{OUT} (typical) = 2.5V

(1) (1) (1) (1)

 I_{OUT} = 300 mA maximum

 P_{DISS} (typical) = 0.240W Temperature Rise = 14.88°C

5.2 Power Calculations

5.2.1 POWER DISSIPATION

The internal power dissipation within the MCP1824/MCP1824S is a function of input voltage, output voltage, output current and quiescent current. Equation 5-1 can be used to calculate the internal power dissipation for the LDO.

EQUATION 5-1:

 $P_{LDO} = (V_{IN(MAX))} - V_{OUT(MIN)}) \times I_{OUT(MAX))}$

Where:

P_{LDO} = LDO Pass device internal

power dissipation

 $V_{IN(MAX)}$ = Maximum input voltage

V_{OUT(MIN)} = LDO minimum output voltage

In addition to the LDO pass element power dissipation, there is power dissipation within the MCP1824/MCP1824S as a result of quiescent or ground current. The power dissipation as a result of the ground current can be calculated using the following equation:

EQUATION 5-2:

 $P_{I(GND)} = V_{IN(MAX)} \times I_{VIN}$

Where:

P_{I(GND} = Power dissipation due to the quiescent current of the LDO

 $V_{IN(MAX)}$ = Maximum input voltage

 I_{VIN} = Current flowing in the V_{IN} pin

with no LDO output current (LDO quiescent current)

The total power dissipated within the MCP1824/ MCP1824S is the sum of the power dissipated in the LDO pass device and the $P(l_{GND})$ term. Because of the CMOS construction, the typical l_{GND} for the MCP1824/ MCP1824S is 120 μA . Operating at a maximum V_{IN} of 3.465V results in a power dissipation of 0.12 milli-Watts for a 2.5V output. For most applications, this is small compared to the LDO pass device power dissipation and can be neglected.

The maximum continuous operating junction temperature specified for the MCP1824/MCP1824S is +125°C. To estimate the internal junction temperature of the MCP1824/MCP1824S, the total internal power dissipation is multiplied by the thermal resistance from junction to ambient (R θ_{JA}) of the device. The thermal resistance from junction to ambient for the SOT-223-5 package is estimated at 62° C/W.

EQUATION 5-3:

 $T_{J(MAX)} = P_{TOTAL} \times R\theta_{JA} + T_{AMAX}$

T_{J(MAX)} = Maximum continuous junction temperature

P_{TOTAL} = Total device power dissipation

 $R\theta_{JA}$ = Thermal resistance from junction to ambient

 T_{AMAX} = Maximum ambient temperature

The maximum power dissipation capability for a package can be calculated given the junction-to-ambient thermal resistance and the maximum ambient temperature for the application. Equation 5-4 can be used to determine the package maximum internal power dissipation.

EQUATION 5-4:

$$P_{D(MAX)} = \frac{(T_{J(MAX)} - T_{A(MAX)})}{R\theta_{JA}}$$

P_{D(MAX)} = Maximum device power dissipation

 $T_{J(MAX)}$ = maximum continuous junction

temperature

 $T_{A(MAX)}$ = maximum ambient temperature

 $R\theta_{JA}$ = Thermal resistance from junction-to-

ambient

EQUATION 5-5:

$$T_{J(RISE)} = P_{D(MAX)} \times R\theta_{JA}$$

T_{J(RISE)} = Rise in device junction temperature over the ambient temperature

 $P_{D(MAX)}$ = Maximum device power dissipation

 $R\theta_{JA}$ = Thermal resistance from junction-to-

ambient

EQUATION 5-6:

$$T_J = T_{J(RISE)} + T_A$$

 T_{\perp} = Junction temperature

T_{J(RISE)} = Rise in device junction temperature over the ambient temperature

 T_A = Ambient temperature

5.3 Typical Application

Internal power dissipation, junction temperature rise, junction temperature, and maximum power dissipation is calculated in the following example. The power dissipation as a result of ground current is small enough to be neglected.

5.3.1 POWER DISSIPATION EXAMPLE

Package

Package Type = SOT-223-5

Input Voltage

 $V_{IN} = 3.3V \pm 5\%$

LDO Output Voltage and Current

 $V_{OUT} = 2.5V$

 $I_{OLIT} = 300 \text{ mA}$

Maximum Ambient Temperature

 $T_{A(MAX)} = 60^{\circ}C$

Internal Power Dissipation

 $P_{LDO(MAX)} = (V_{IN(MAX)} - V_{OUT(MIN)}) \times I_{OUT(MAX)}$

 $P_{LDO} = ((3.3 \text{V} \times 1.05) - (2.5 \text{V} \times 0.975))$

x 300 mA

 $P_{LDO} = 0.308 \text{ Watts}$

5.3.1.1 Device Junction Temperature Rise

The internal junction temperature rise is a function of internal power dissipation and the thermal resistance from junction-to-ambient for the application. The thermal resistance from junction-to-ambient (R θ_{JA}) is derived from EIA/JEDEC standards for measuring thermal resistance. The EIA/JEDEC specification is JESD51. The standard describes the test method and board specifications for measuring the thermal resistance from junction to ambient. The actual thermal resistance for a particular application can vary depending on many factors such as copper area and thickness. Refer to AN792, "A Method to Determine How Much Power a SOT23 Can Dissipate in an Application" (DS00792), for more information regarding this subject.

 $T_{J(RISE)} = P_{TOTAL} \times R\theta_{JA}$

 $T_{JRISE} = 0.308 \text{ W x } 62^{\circ} \text{ C/W}$

 $T_{JRISF} = 19.1$ °C

5.3.1.2 Junction Temperature Estimate

To estimate the internal junction temperature, the calculated temperature rise is added to the ambient or offset temperature. For this example, the worst-case junction temperature is estimated below:

$$T_J = T_{JRISE} + T_{A(MAX)}$$

 $T_J = 19.1^{\circ}C + 60.0^{\circ}C$
 $T_J = 79.1^{\circ}C$

5.3.1.3 Maximum Package Power Dissipation at 60°C Ambient Temperature

SOT-223-5 (62°C/W Rθ_{JA}):

$$P_{D(MAX)} = (125^{\circ}C - 60^{\circ}C) / 62^{\circ}C/W$$

 $P_{D(MAX)} = 1.048W$

SOT-23-5 (256°C/Watt $R\theta_{JA}$):

$$P_{D(MAX)} = (125^{\circ}C - 60^{\circ}C)/256^{\circ}C/W$$

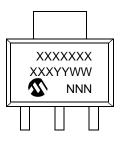
 $P_{D(MAX)} = 0.254W$

From this table, you can see the difference in maximum allowable power dissipation between the SOT-223-5 package and the SOT-23-5 package.

6.0 PACKAGING INFORMATION

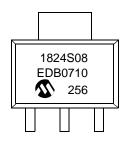
6.1 Package Marking Information

3-Lead SOT-223 (MCP1824S)



Part Number	Marking Code
MCP1824ST-0802E/DB	1824S08
MCP1824ST-1202E/DB	1824S12
MCP1824ST-1802E/DB	1824S18
MCP1824ST-2502E/DB	1824S25
MCP1824ST-3002E/DB	1824S30
MCP1824ST-3302E/DB	1824S33
MCP1824ST-5002E/DB	1824S50

Example:



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

(e3) Pb-free JEDEC designator for Matte Tin (Sn)

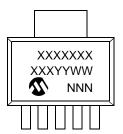
This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

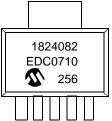
Package Marking Information (Continued)

5-Lead SOT-223 (MCP1824)

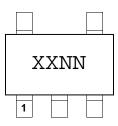


Part Number	Marking Code
MCP1824T-0802E/DC	1824082
MCP1824T-1202E/DC	1824122
MCP1824T-1802E/DC	1824182
MCP1824T-2502E/DC	1824252
MCP1824T-3002E/DC	1824302
MCP1824T-3302E/DC	1824332
MCP1824T-5002E/DC	1824502
MCP1824T-ADJE/DC	1824ADJ

Example:

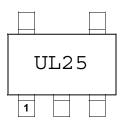


5-Lead SOT-23



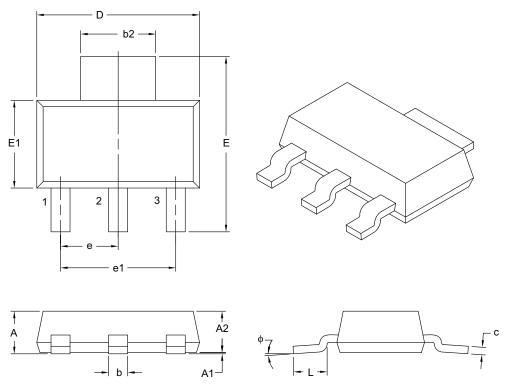
Part Number	Marking Code
MCP1824T-0802E/OT	ULNN
MCP1824T-1202E/OT	UMNN
MCP1824T-1802E/OT	UPNN
MCP1824T-2502E/OT	UQNN
MCP1824T-3002E/OT	URNN
MCP1824T-3302E/OT	USNN
MCP1824T-5002E/OT	UTNN
MCP1824T-ADJE/OT	UKNN

Example:



3-Lead Plastic Small Outline Transistor (DB) [SOT-223]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX		
Number of Leads	N		3			
Lead Pitch	е		2.30 BSC			
Outside Lead Pitch	e1		4.60 BSC			
Overall Height	A	_	_	1.80		
Standoff	A1	0.02	_	0.10		
Molded Package Height	A2	1.50	1.60	1.70		
Overall Width	E	6.70	7.00	7.30		
Molded Package Width	E1	3.30	3.50	3.70		
Overall Length	D	6.30	6.50	6.70		
Lead Thickness	С	0.23	0.30	0.35		
Lead Width	b	0.60	0.76	0.84		
Tab Lead Width	b2	2.90	3.00	3.10		
Foot Length	L	0.75	_	_		
Lead Angle	ф	0°	_	10°		

Notes:

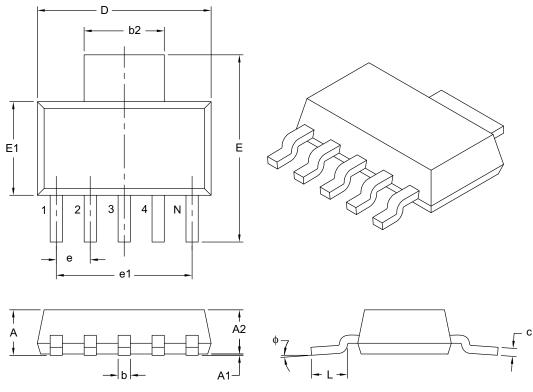
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-032B

5-Lead Plastic Small Outline Transistor (DC) [SOT-223]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX		
Number of Leads	N		5	•		
Lead Pitch	е		1.27 BSC			
Outside Lead Pitch	e1		5.08 BSC			
Overall Height	A	1.80				
Standoff	A1	0.02	0.06	0.10		
Molded Package Height	A2	1.55	1.60	1.65		
Overall Width	E	6.86	7.00	7.26		
Molded Package Width	E1	3.45	3.50	3.55		
Overall Length	D	6.45	6.50	6.55		
Lead Thickness	С	0.24	0.28	0.32		
Lead Width	b	0.41	0.457	0.51		
Tab Lead Width	b2	2.95	3.00	3.05		
Foot Length	L	0.91	_	1.14		
Lead Angle	ф	0°	4°	8°		

Notes:

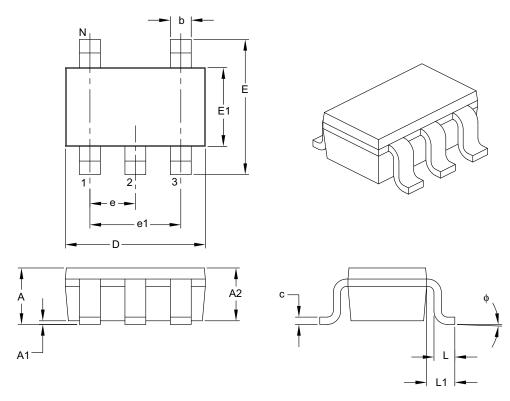
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-137B

5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS				
Dimension	Dimension Limits		NOM	MAX		
Number of Pins	N	5				
Lead Pitch	е	0.95 BSC				
Outside Lead Pitch	e1	1.90 BSC				
Overall Height	Α	0.90	_	1.45		
Molded Package Thickness	A2	0.89	_	1.30		
Standoff	A1	0.00	_	0.15		
Overall Width	E	2.20	_	3.20		
Molded Package Width	E1	1.30	_	1.80		
Overall Length	D	2.70	_	3.10		
Foot Length	L	0.10	_	0.60		
Footprint	L1	0.35	_	0.80		
Foot Angle	ф	0°	_	30°		
Lead Thickness	С	0.08	_	0.26		
Lead Width	b	0.20	_	0.51		

Notes:

- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

APPENDIX A: REVISION HISTORY

Revision A (November 2007)

• Original Release of this Document.

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. Device	XX Output Voltage		X T Tolerance	<u>X/</u> Temp.	XX Package	
Dovice:		MCD1924	200 m \ Lo	u Drono	ıt Bogulotor	

Device: 300 mA Low Dropout Regulator MCP1824T: 300 mA Low Dropout Regulator

Tape and Reel

MCP1824S: 300 mA Low Dropout Regulator MCP1824ST: 300 mA Low Dropout Regulator

Tape and Reel

Output Voltage *: 80 = 0.8V "Standard"

12 = 1.2V "Standard" = 1.8V "Standard" 18 = 2.5V "Standard" 25 = 3.0V "Standard" 30 = 3.3V "Standard" 33 = 5.0V "Standard" 50

ADJ = Adjustable Output Voltage ** (MCP1824 Only)

*Contact factory for other output voltage options ** When ADJ is used, the "extra feature code" and "tolerance" columns do not apply. Refer to examples.

Extra Feature Code: = Fixed

Tolerance: = 2.5% (Standard)

Temperature: = -40°C to +125°C

Package Type: = Plastic Small Transistor Outline, SOT-223, 3-lead

= Plastic Small Transistor Outline, SOT-223, 5-lead = Plastic Small Transistor Outline, SOT-23, 5-lead

Note: ADJ (Adjustable) only available in 5-lead version.

Examples:

MCP1824-0802E/XX: 0.8V LDO Regulator

MCP1824-1002E/XX: 1.0V LDO Regulator

c) MCP1824-1202E/XX: 1.2V LDO Regulator

MCP1824-1802E/XX: 1.8V LDO Regulator

MCP1824-2502E/XX: 2.5V LDO Regulator e)

f) MCP1824-3002E/XX: 3.0V LDO Regulator

MCP1824-3302E/XX: 3.3V LDO Regulator g)

h) MCP1824-5002E/XX: 5.0V LDO Regulator

i) MCP1824-ADJE/XX: ADJ LDO Regulator

a) MCP1824S-0802E/XX:0.8V LDO Regulator

b) MCP1824S-1002E/XX:1.0V LDO Regulator

c) MCP1824S-1202E/XX:1.2V LDO Regulator

d) MCP1824S-1802E/XX:1.8V LDO Regulator

e)

MCP1824S-2502E/XX:2.5V LDO Regulator

f) MCP1824S-2502E/XX:3.0V LDO Regulator g) MCP1824S-3302E/XX:3.3V LDO Regulator

h) MCP1824S-5002E/XX:5.0V LDO Regulator

DB for 3LD SOT-223 package XX =

DC for 5LD SOT-223 package

OT for 5LD SOT-23 package

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the
 intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, Accuron, dsPIC, KEELOQ, KEELOQ logo, microID, MPLAB, PIC, PICmicro, PICSTART, PRO MATE, rfPIC and SmartShunt are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AmpLab, FilterLab, Linear Active Thermistor, Migratable Memory, MXDEV, MXLAB, SEEVAL, SmartSensor and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, dsSPEAK, ECAN, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, Mindi, MiWi, MPASM, MPLAB Certified logo, MPLIB, MPLINK, PICkit, PICDEM, PICDEM.net, PICLAB, PICtail, PowerCal, PowerInfo, PowerMate, PowerTool, REAL ICE, rfLAB, Select Mode, Smart Serial, SmartTel, Total Endurance, UNI/O, WiperLock and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2007, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

QUALITY MANAGEMENT SYSTEM

CERTIFIED BY DNV

ISO/TS 16949:2002

Microchip received ISO/TS-16949:2002 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277

Technical Support:

http://support.microchip.com

Web Address: www.microchip.com

Atlanta

Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Boston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca. IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

Kokomo, IN Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara

Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto

Mississauga, Ontario,

Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office

Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon

Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney

Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing Tel: 86-10-8528-2100

Fax: 86-10-8528-2104

China - Chengdu

Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Fuzhou

Tel: 86-591-8750-3506 Fax: 86-591-8750-3521

China - Hong Kong SAR

Tel: 852-2401-1200 Fax: 852-2401-3431

China - Nanjing

Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

China - Qingdao

Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Shunde

Tel: 86-757-2839-5507 Fax: 86-757-2839-5571

China - Wuhan

Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian

Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

ASIA/PACIFIC

India - Bangalore

Tel: 91-80-4182-8400 Fax: 91-80-4182-8422

India - New Delhi

Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune

Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

Japan - Yokohama

Tel: 81-45-471-6166 Fax: 81-45-471-6122

Korea - Daegu

Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur

Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang

Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila Tel: 63-2-634-9065

Fax: 63-2-634-9069

Singapore

Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu

Tel: 886-3-572-9526 Fax: 886-3-572-6459

Taiwan - Kaohsiung

Tel: 886-7-536-4818 Fax: 886-7-536-4803

Taiwan - Taipei

Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Thailand - Bangkok

Tel: 66-2-694-1351 Fax: 66-2-694-1350

EUROPE

Austria - Wels

Tel: 43-7242-2244-39 Fax: 43-7242-2244-393

Denmark - Copenhagen Tel: 45-4450-2828

Fax: 45-4450-2828

France - Paris

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Munich

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen

Tel: 31-416-690399 Fax: 31-416-690340 **Spain - Madrid**

Tel: 34-91-708-08-90

Fax: 34-91-708-08-91 **UK - Wokingham**

Tel: 44-118-921-5869 Fax: 44-118-921-5820

10/05/07